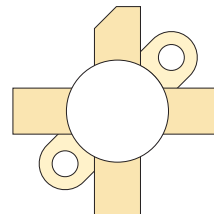


RF POWER VERTICAL MOSFET

The VRF148A is a gold-metallized silicon n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, or inter-modulation distortion.



FEATURES

- Improved Ruggedness $V_{(BR)DSS} = 170V$
- 30W with 20dB Typical Gain @ 30MHz, 50V
- 30W with 16dB Typical Gain @ 175MHz, 50V
- Excellent Stability & Low IMD
- Common Source Configuration
- Available in Matched Pairs
- 30:1 Load VSWR Capability at Specified Operating Conditions
- Nitride Passivated
- Refractory Gold Metallization
- High Voltage Replacement for MRF148A
- RoHS Compliant 

Maximum Ratings

All Ratings: $T_c = 25^\circ C$ unless otherwise specified

Symbol	Parameter	VRF148A(MP)	Unit
V_{DSS}	Drain-Source Voltage	170	V
I_D	Continuous Drain Current @ $T_c = 25^\circ C$	6	A
V_{GS}	Gate-Source Voltage	± 40	V
P_D	Total Device dissipation @ $T_c = 25^\circ C$	115	W
T_{STG}	Storage Temperature Range	-65 to 150	$^\circ C$
T_J	Operating Junction Temperature	200	

Static Electrical Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 1mA$)	170			V
$V_{DS(ON)}$	On State Drain Voltage ($I_{D(ON)} = 2.5A, V_{GS} = 10V$)		3.0	5.0	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 100V, V_{GS} = 0V$)			0.1	mA
I_{GSS}	Gate-Source Leakage Current ($V_{DS} = \pm 20V, V_{GS} = 0V$)			1.0	μA
g_{fs}	Forward Transconductance ($V_{DS} = 10V, I_D = 2.5A$)	0.8			mhos
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = 10V, I_D = 10mA$)	2.9	3.6	4.4	V

Thermal Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			1.52	$^\circ C/W$



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Dynamic Characteristics

VRF148A(MP)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		160		pF
C_{oss}	Output Capacitance	$V_{DS} = 50V$		40		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		2.6		

Functional Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
G _{PS}	f ₁ = 30MHz, V _{DD} = 50V, I _{DQ} = 100mA, P _{out} = 30W		18		dB
G _{PS}	f ₁ = 175MHz, V _{DD} = 50V, I _{DQ} = 100mA, P _{out} = 30W		16		
η	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 50V, I _{DQ} = 100mA, 30 W _{PEP}		40		%
η	f ₁ = 30MHz, V _{DD} = 50V, I _{DQ} = 100mA, 30 W _{CW}		50		
IMD _(d3)	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 50V, I _{DQ} = 100mA, P _{out} = 30W _{PEP} ¹		-35	-28	dB
IMD _(d11)	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 50V, I _{DQ} = 100mA, P _{out} = 30W _{PEP}		-60		
ψ	f ₁ = 30MHz, f ₂ = 30.001MHz, V _{DD} = 50V, I _{DQ} = 100mA, P _{out} = 300W _{PEP} 30:1 VSWR - All Phase Angles	No Degradation in Output Power			

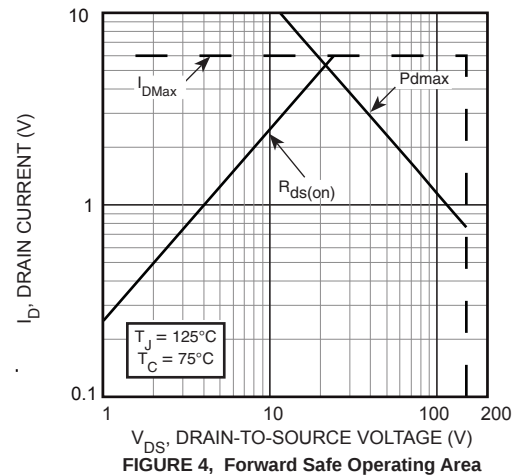
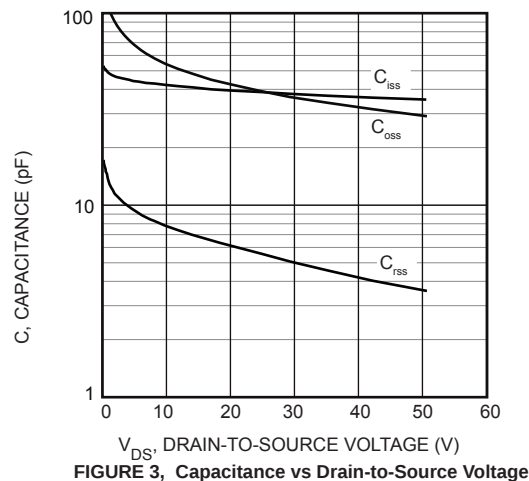
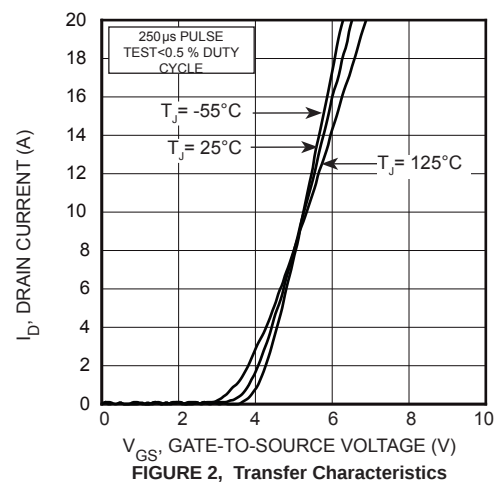
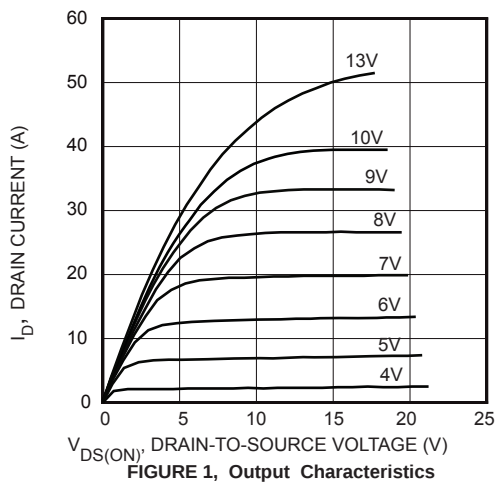
Class A Characteristics

Symbol	Test Conditions	Min	Typ	Max	Unit
G_{PS}	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 1.0A, P_{out} = 10W_{PEP}$		20		dB
IMD _(d3)	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 1.0A, P_{out} = 10W_{PEP}$		-50		
IMD _(d9-d13)	$f_1 = 30MHz, f_2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 1.0A, P_{out} = 10W_{PEP}$		-70		

1. To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves



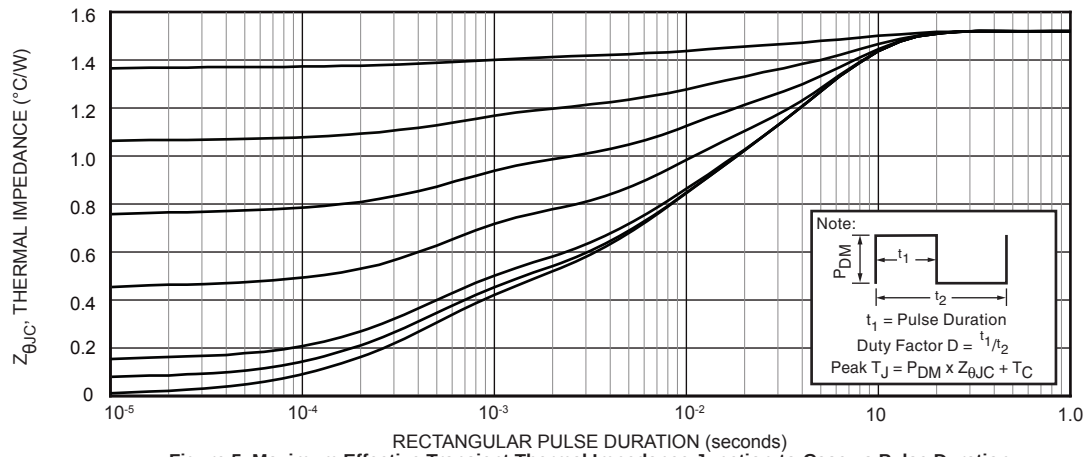


Figure 5. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

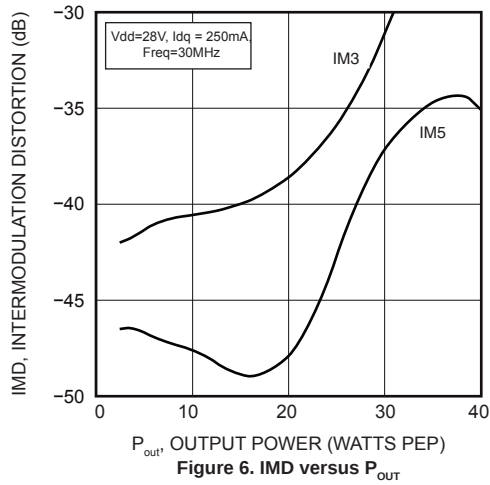


Figure 6. IMD versus P_{OUT}

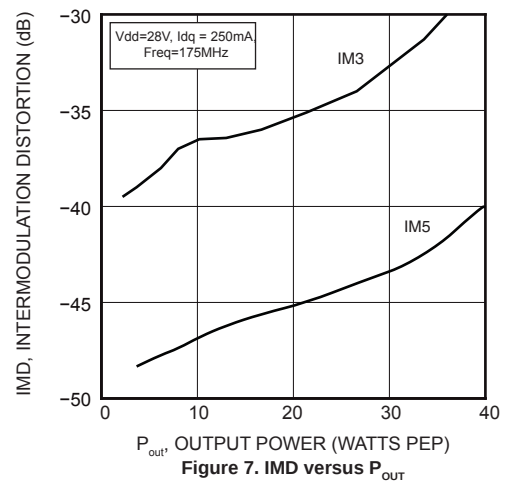


Figure 7. IMD versus P_{OUT}

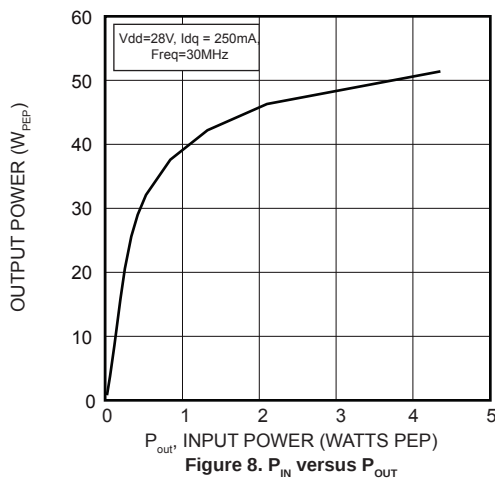


Figure 8. P_{IN} versus P_{OUT}

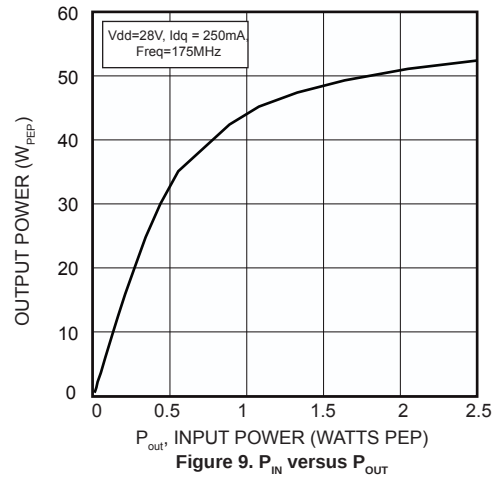
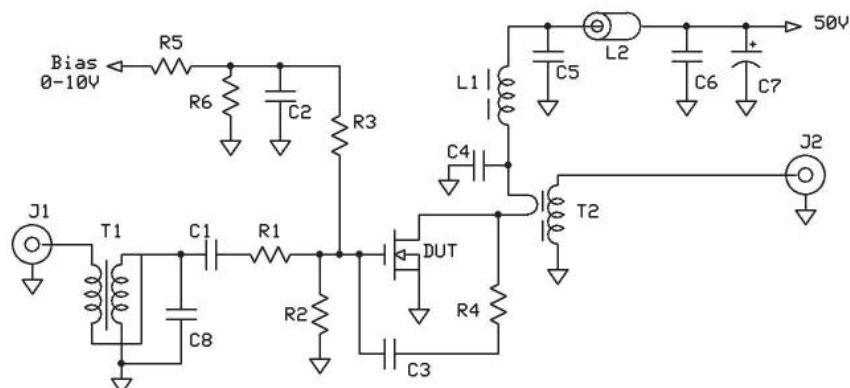


Figure 9. P_{IN} versus P_{OUT}

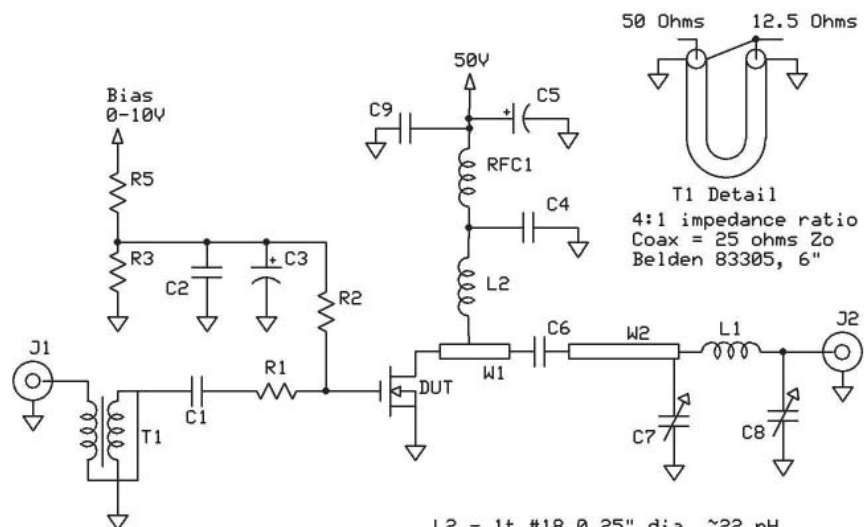
30 MHz test circuit



C1-C6 - 0.1uF 100V SMT
 C7 - 15uF 100V Elect
 C8 - 100 pF ATC 100B
 T1 - 4:1 transformer
 T2 = 2:3 turns ratio on two
 ferrite beads u=125

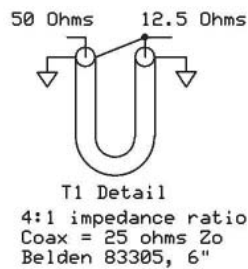
L1 Fair-Rite 2961666631 (VK200-4B)
 L2 - two ferrite beads on #18
 R1 - 4.7 ohm 1/4W
 R2 R3 - 200 ohm 1/2 Carbon
 R4 - 470 ohm 1W
 R5 R6 - 2200 ohm 1/4W

175 MHz test circuit



C1 - 91pF ATC 100B
 C2,4,6,9 - 0.1uF 100V 1206 SMT
 C3 - 1 uF 50 WV tant
 C5 - 15uF 100V Elect
 C7 C8 - ARCO 404 ~20pF
 L1 - 1t #18 0.25" dia ~25nH

L2 - 1t #18 0.25" dia ~22 nH
 R1 - 1 ohm 1/4W
 R2 R3 R5 - 2200 ohm 1/4W
 RFC1 Fair-Rite 2961666631 (VK200-4B)
 T1 - 4:1 transformer
 W1 Stripline .23 x 0.50"
 W2 Stripline 1.2" x .122" (50 ohm)

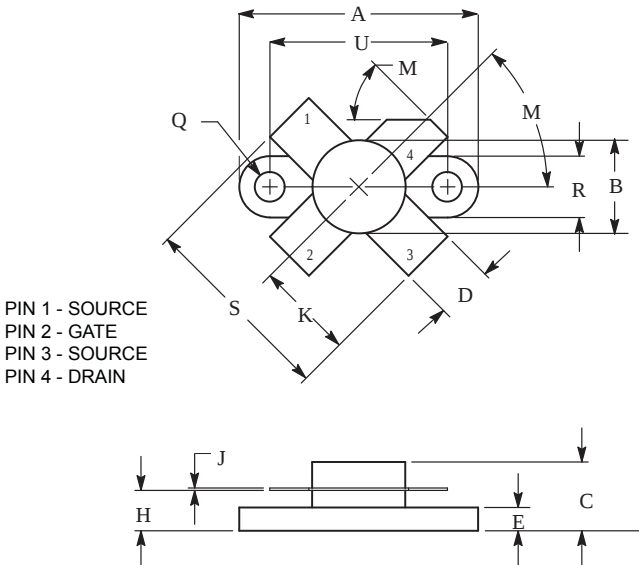


Adding MP at the end of P/N specifies a matched pair where $V_{GS(TH)}$ is matched between the two parts. V_{TH} values are marked on the devices per the following table.

Code	Vth Range	Code 2	Vth Range
A	2.900 - 2.975	M	3.650 - 3.725
B	2.975 - 3.050	N	3.725 - 3.800
C	3.050 - 3.125	P	3.800 - 3.875
D	3.125 - 3.200	R	3.875 - 3.950
E	3.200 - 3.275	S	3.950 - 4.025
F	3.275 - 3.350	T	4.025 - 4.100
G	3.350 - 3.425	W	4.100 - 4.175
H	3.425 - 3.500	X	4.175 - 4.250
J	3.500 - 3.575	Y	4.250 - 4.325
K	3.575 - 3.650	Z	4.325 - 4.400

V_{TH} values are based on Microsemi measurements at datasheet conditions with an accuracy of 1.0%.

M113 Package Outline .375" SOE
All Dimensions to be $\pm .005$



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.096	0.990	24.39	25.14
B	0.370	0.390	9.40	9.90
C	0.229	0.281	5.82	7.13
D	0.215	0.235	5.47	5.96
E	0.085	0.105	2.16	2.66
H	0.150	0.108	3.81	4.57
J	0.004	0.006	0.11	0.15
K	0.395	0.405	10.04	10.28
M	40	50	40	50
Q	0.113	0.130	2.88	3.30
R	0.245	0.255	6.23	6.47
S	0.790	0.810	20.07	20.57
U	0.720	0.730	18.29	18.54